

FEATURES

Complementary type the PNP transistor

A1015 is recommended.

MARKING: HF
MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	150	mA
Collector Power Dissipation	P_C	0.2	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

C1815 (NPN)

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=0.1mA, I_B=0$	50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Collector cut-off current	I_{CE}	$V_{CE}=50V, I_B=0$			0.1	μA
Emitter cut-off current	I_{EB}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=2mA$	130		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=1mA, f=30MHz$	80			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H	
Range	130-200	200-400	

C1815 Typical Characteristics

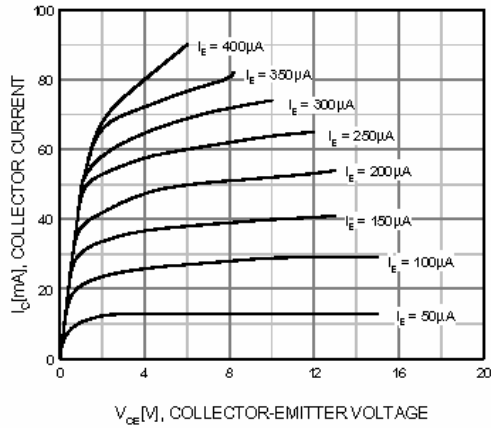


Figure 1. Static Characteristic

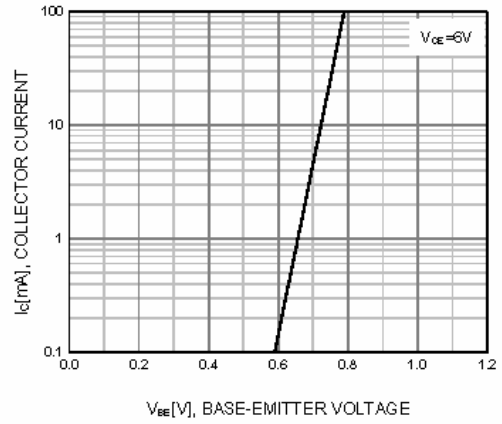


Figure 2. Transfer Characteristic

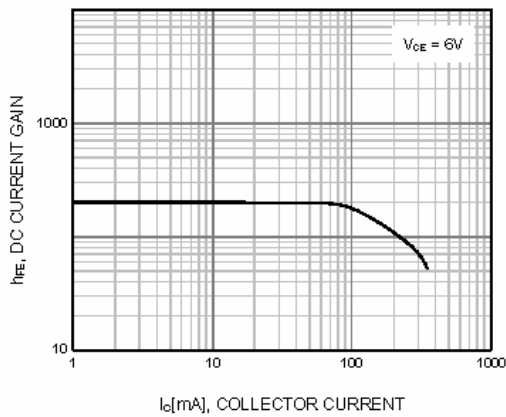
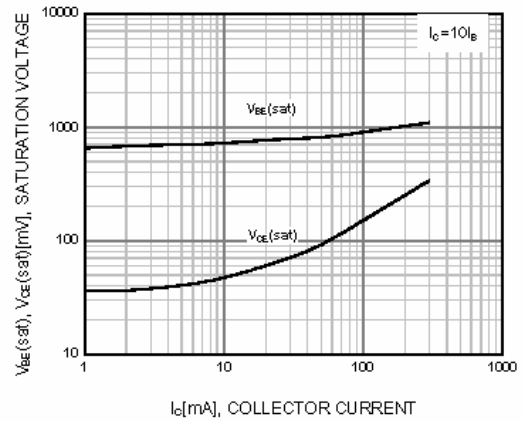


Figure 3. DC current Gain



**Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

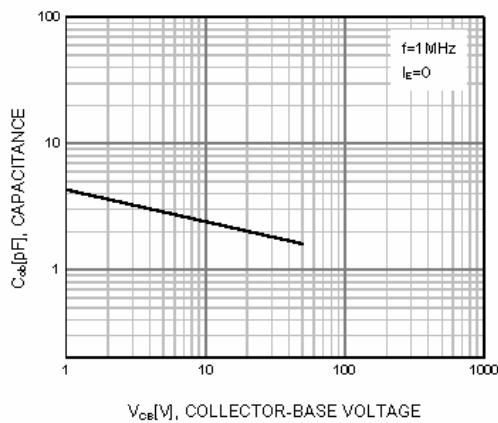


Figure 5. Output Capacitance

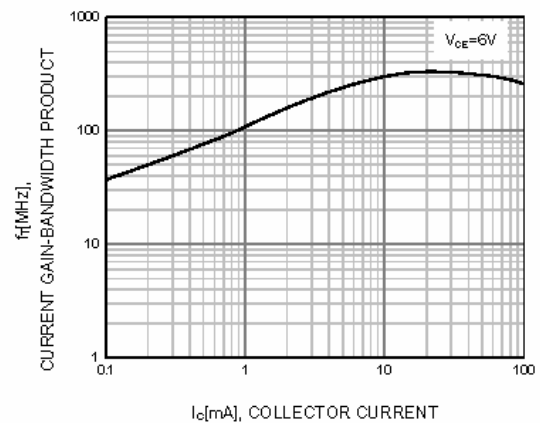


Figure 6. Current Gain Bandwidth Product